10-EZ07PMA030I7-L926A28T
datasheet

***flow*PIM E1** **650 V / 30 A**

Topology features

- Open Emitter configuration
- Temperature sensor
- Converter+Brake+Inverter

Component features

- Easy paralleling
- Low collector emitter saturation voltage
- Low turn-off losses
- Positive temperature coefficient

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Solder pin

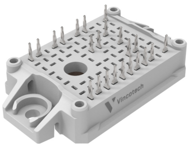
Target applications

- Industrial Drives

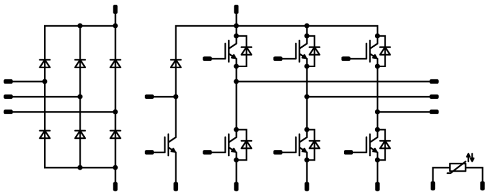
Types

- 10-EZ07PMA030I7-L926A28T

flow E1 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ T_s = 80 °C	40	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	66	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 400 V T_j = 150 °C	3	μs
Maximum junction temperature	T_{jmax}		175	°C
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	38	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	61	W
Maximum junction temperature	T_{jmax}		175	°C
Brake Switch				
Collector-emitter voltage	V_{CES}		650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ T_s = 80 °C	40	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	90	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	66	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 400 V T_j = 150 °C	3	μs
Maximum junction temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Brake Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	28	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	50	W
Maximum junction temperature	T_{jmax}		175	°C
Rectifier Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	47	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms T_j = 150 °C	270	A
Surge current capability	I^2t		370	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	61	W
Maximum junction temperature	T_{jmax}		150	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Creepage distance			>12,7	mm
Clearance			>12,7	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production

Characteristic Values

Parameter	**Symbol**	**Conditions**					**Values**			**Unit**
			V_{GE} **[V]** V_{GS} **[V]**	V_{CE} **[V]** V_{DS} **[V]** V_F **[V]**	I_C **[A]** I_D **[A]** I_F **[A]**	T_j **[°C]**	**Min**	**Typ**	**Max**	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0003	25	4,35	5	5,65	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 125 150		1,3 1,37 1,39	1,65[1]	V
Collector-emitter cut-off current	I_{CES}		0	650		25			20	μA
Gate-emitter leakage current	I_{GES}		0	650		25			100	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1900		pF
Output capacitance	C_{oes}							62		pF
Reverse transfer capacitance	C_{res}							20		pF
Gate charge	Q_g	V_{CC} = 520 V	15		30	25		180		nC
Thermal										
Thermal resistance junction to sink[2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,45		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	±15	350	40	25 125 150		121,73 125,39 126,41		ns
Rise time	t_r					25 125 150		44,03 43,86 43,11		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		150,47 176,6 182,17		ns
Fall time	t_f					25 125 150		34,48 64,88 71,91		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,549 μC Q_{rFWD}=1,33 μC Q_{rFWD}=1,57 μC				25 125 150		1,17 1,52 1,62		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,633 0,973 1,08		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_{F} [V]	I_{C} [A] I_{D} [A] I_{F} [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				30	25 125 150		1,63 1,53 1,5	2(1)	V
Reverse leakage current	I_R	V_r = 650 V				25			20	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,56		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=625 A/µs di/dt=522 A/µs di/dt=599 A/µs	±15	350	40	25 125 150		8,51 14,04 15,31		A
Reverse recovery time	t_{rr}					25 125 150		94,96 142,55 157,9		ns
Recovered charge	Q_r					25 125 150		0,549 1,33 1,57		µC
Reverse recovered energy	E_{rec}					25 125 150		0,086 0,237 0,283		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		785,89 296,08 209,55		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0003	25	4,35	5	5,65	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 125 150		1,3 1,37 1,39	1,65[1]	V
Collector-emitter cut-off current	I_{CES}		0	650		25			20	µA
Gate-emitter leakage current	I_{GES}		0	650		25			100	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		1900		pF
Output capacitance	C_{oes}							62		pF
Reverse transfer capacitance	C_{res}							20		pF
Gate charge	Q_g	V_{CC} = 520 V	15		30	25		180		nC
Thermal										
Thermal resistance junction to sink[2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,45		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	0/15	400	40	25 125 150		29,53 32,7 33,3		ns
Rise time	t_r					25 125 150		40,52 42,98 43,05		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		322,21 350,45 357,62		ns
Fall time	t_f					25 125 150		22,66 29,66 30,75		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,447 µC Q_{rFWD}=1,04 µC Q_{rFWD}=1,22 µC				25 125 150		1,31 1,7 1,77		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,844 1,16 1,28		mWs

Characteristic Values

Parameter	**Symbol**	**Conditions**					**Values**			**Unit**
			V_{GE} **[V]** V_{GS} **[V]**	V_{CE} **[V]** V_{DS} **[V]** V_{F} **[V]**	I_{C} **[A]** I_{D} **[A]** I_{F} **[A]**	T_j **[°C]**	**Min**	**Typ**	**Max**	
Brake Diode										
Static										
Forward voltage	V_F				20	25 125 150		1,71 1,6 1,55	2(1)	V
Reverse leakage current	I_R	V_r = 650 V				25			20	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,9		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=523 A/µs d*i*/d*t*=609 A/µs d*i*/d*t*=557 A/µs	0/15	400	40	25 125 150		6,84 10,85 11,7		A
Reverse recovery time	t_{rr}					25 125 150		94,94 140,32 157,52		ns
Recovered charge	Q_r					25 125 150		0,447 1,04 1,22		µC
Reverse recovered energy	E_{rec}					25 125 150		0,081 0,209 0,252		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		241,94 195,24 161,14		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Rectifier Diode										
Static										
Forward voltage	V_F				28	25 125		1,15 1,1	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,15		K/W
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 499 Ω				100	3,2		3,3	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3380		K
Vincotech Thermistor Reference									V	

(1) Value at chip level

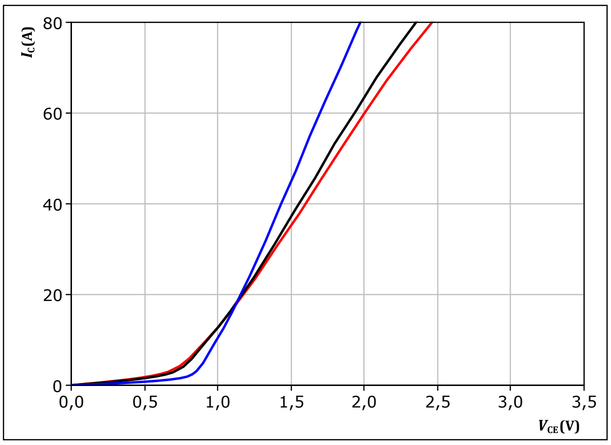
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

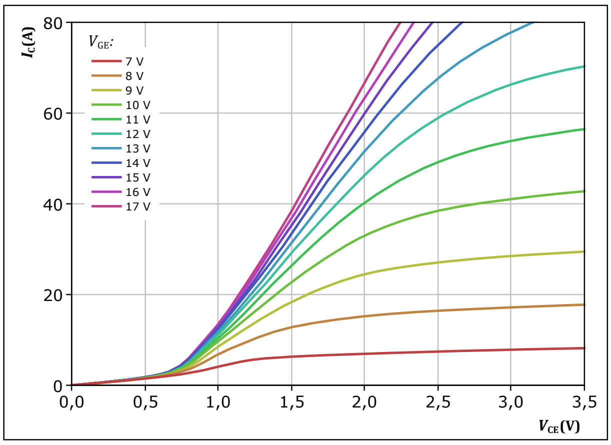


t_p = 250 μs
V_{GE} = 15 V
T_j: 25 °C
125 °C
150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

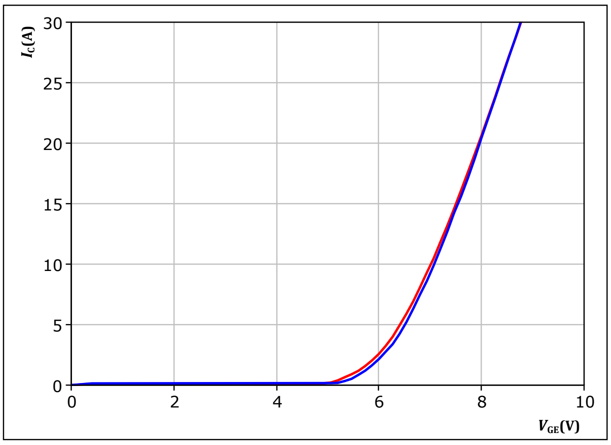


t_p = 250 μs
T_j = 150 °C
V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

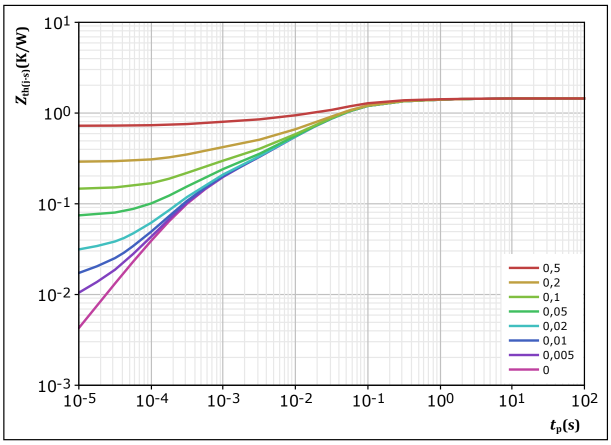


t_p = 250 μs
V_{CE} = 9 V
T_j: 125 °C
150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T
$R_{th(j-s)}$ = 1,448 K/W

IGBT thermal model values

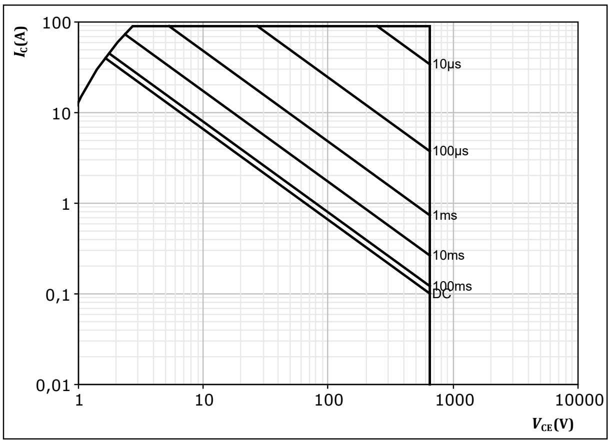
R (K/W)	τ (s)
8,39E-02	1,48E+00
2,97E-01	1,38E-01
7,21E-01	3,10E-02
2,11E-01	3,93E-03
1,36E-01	3,86E-04

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})

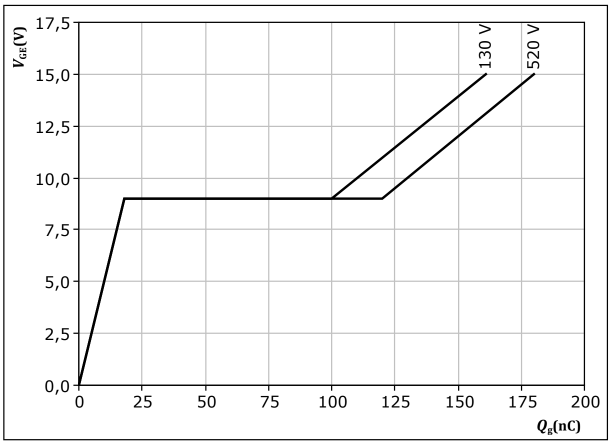


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 6. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



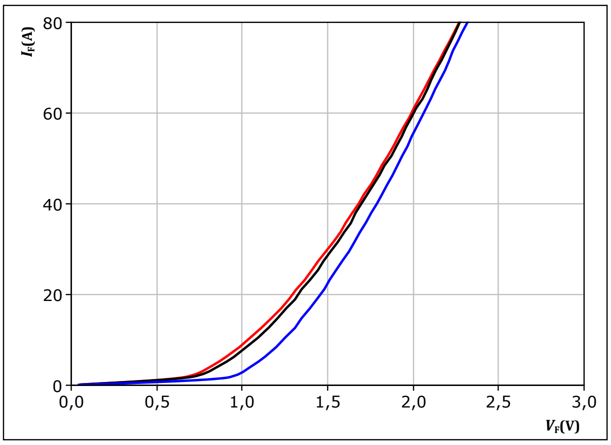
I_C = 30 A
T_j = 25 °C

Inverter Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

I_F = f(V_F)



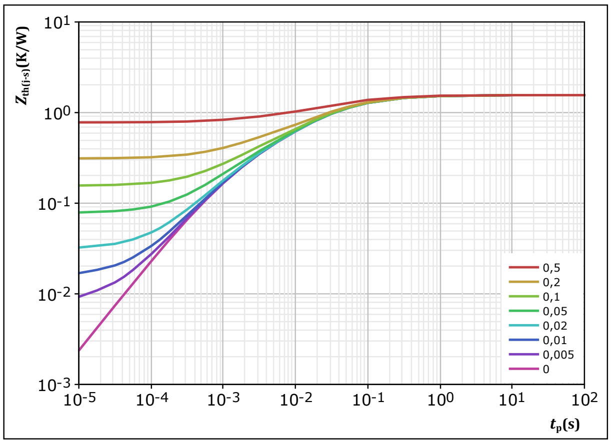
t_p = 250 µs

T_j: 25 °C
125 °C
150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,558 K/W

FWD thermal model values

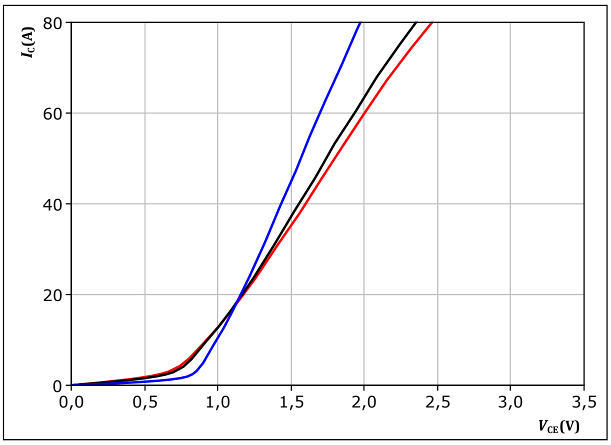
R (K/W)	τ (s)
4,84E-02	3,08E+00
3,87E-01	1,73E-01
7,62E-01	2,49E-02
2,92E-01	3,18E-03
6,90E-02	6,08E-04

Brake Switch Characteristics

figure 9. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



t_p = 250 µs

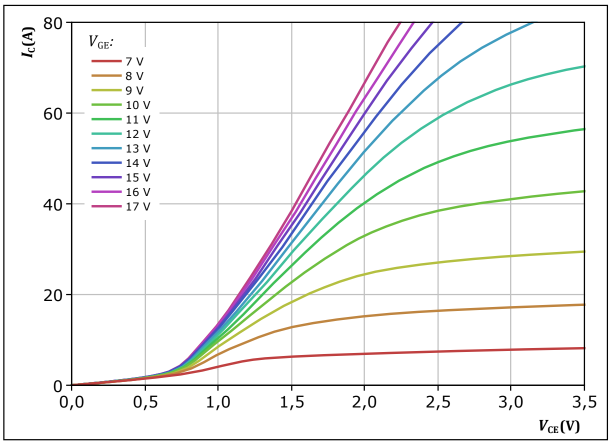
V_{GE} = 15 V

T_j: 25 °C
125 °C
150 °C

figure 10. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



t_p = 250 µs

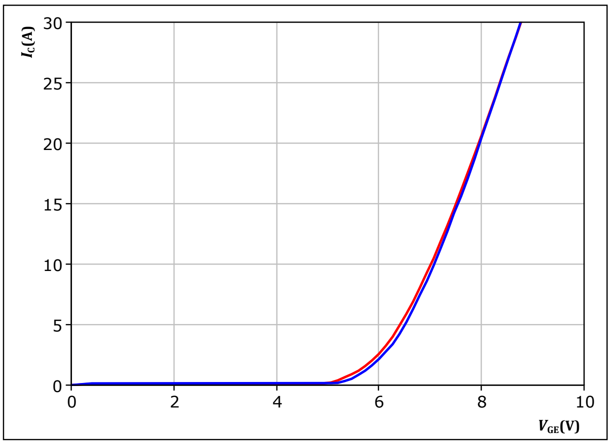
T_j = 150 °C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 11. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



t_p = 250 µs

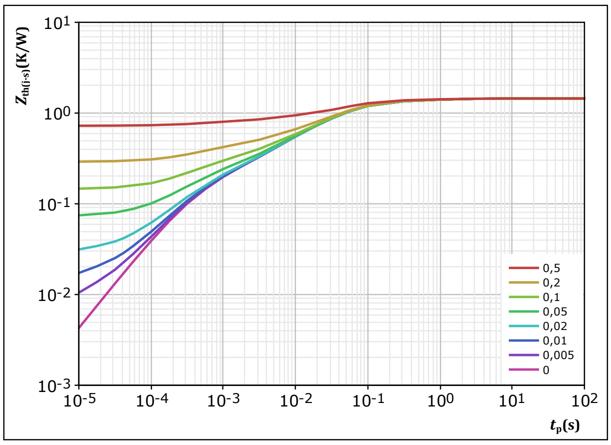
V_{CE} = 9 V

T_j: 125 °C
150 °C

figure 12. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,448 K/W

IGBT thermal model values

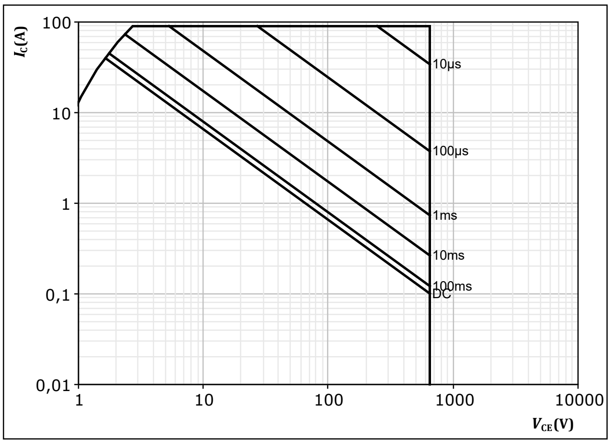
R (K/W)	τ (s)
8,39E-02	1,48E+00
2,97E-01	1,38E-01
7,21E-01	3,10E-02
2,11E-01	3,93E-03
1,36E-01	3,86E-04

Brake Switch Characteristics

figure 13. **IGBT**

Safe operating area

I_C = f(V_{CE})



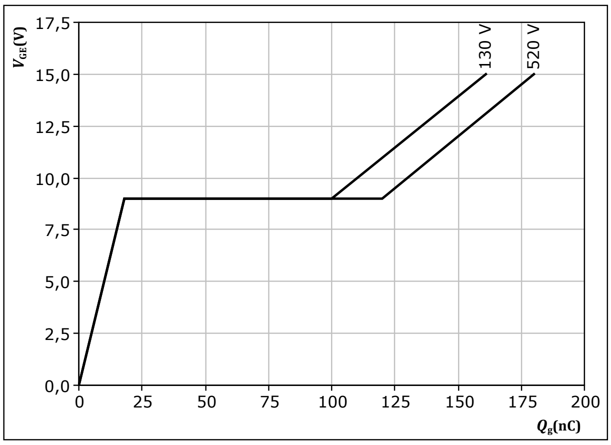
D = single pulse

T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

figure 14. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



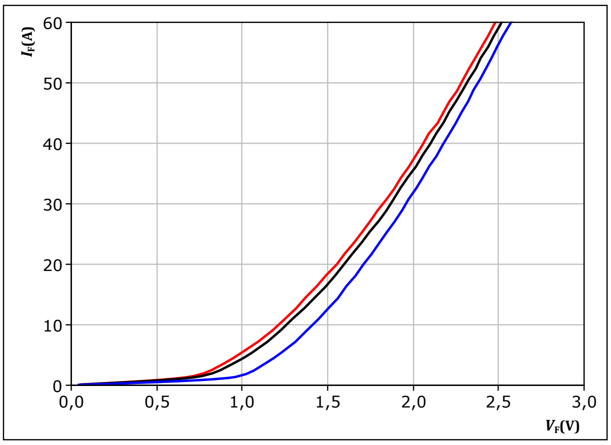
I_C =	30	A
T_j =	25	°C

Brake Diode Characteristics

figure 15. **FWD**

Typical forward characteristics

I_F = f(V_F)



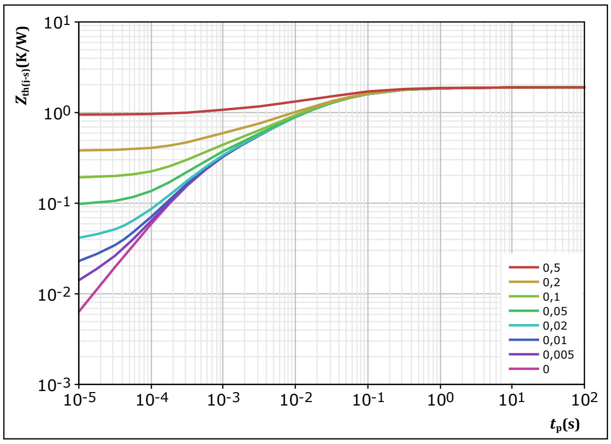
t_p = 250 µs

T_j:
25 °C
125 °C
150 °C

figure 16. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,899 K/W

FWD thermal model values

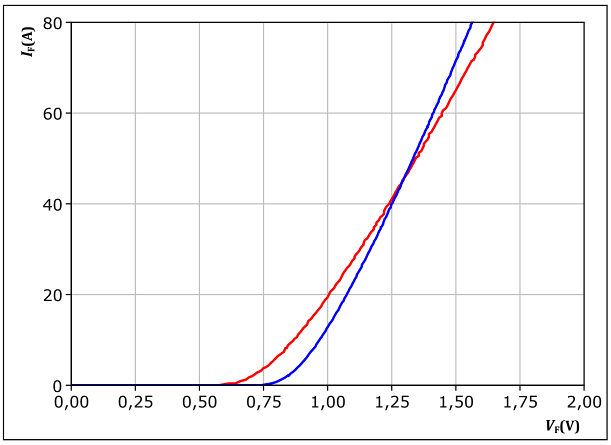
R (K/W)	τ (s)
6,60E-02	3,50E+00
4,15E-01	1,56E-01
7,82E-01	2,46E-02
4,19E-01	3,71E-03
2,17E-01	4,40E-04

Rectifier Diode Characteristics

figure 17. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



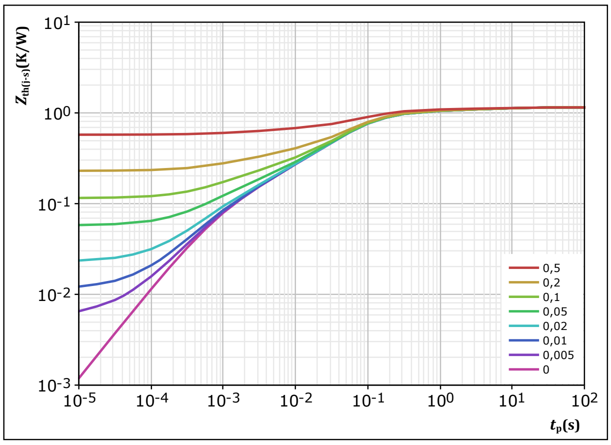
t_p = 250 μs

T_j: 25 °C, 125 °C

figure 18. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,149 K/W

Rectifier thermal model values

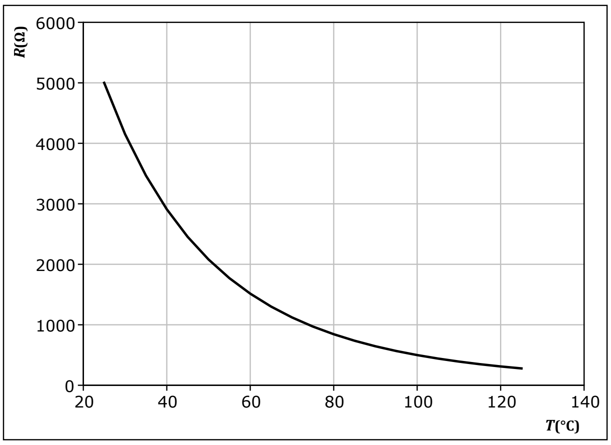
R (K/W)	τ (s)
8,29E-02	7,59E+00
1,02E-01	6,72E-01
4,20E-01	1,19E-01
3,78E-01	4,22E-02
1,08E-01	4,04E-03
5,78E-02	7,21E-04

Thermistor Characteristics

figure 19. **Thermistor**

Typical NTC characteristic as function of temperature

R_T = f(T)

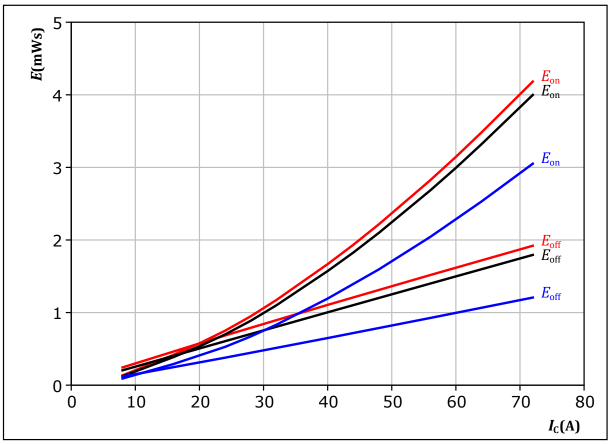


Inverter Switching Characteristics

figure 20. **IGBT**

Typical switching energy losses as a function of collector current

E = f(I_C)



With an inductive load at

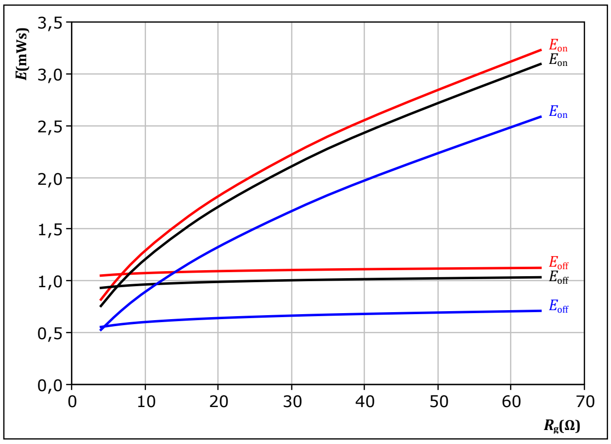
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 16 Ω
R_{goff} = 16 Ω

T_j:
25 °C
125 °C
150 °C

figure 21. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

E = f(R_g)



With an inductive load at

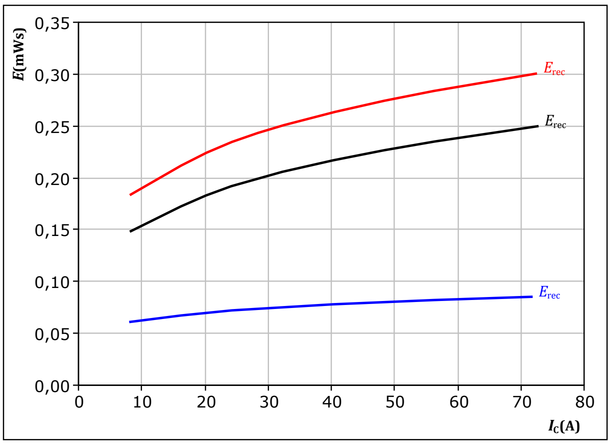
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

T_j:
25 °C
125 °C
150 °C

figure 22. **FWD**

Typical reverse recovered energy loss as a function of collector current

E_{rec} = f(I_C)



With an inductive load at

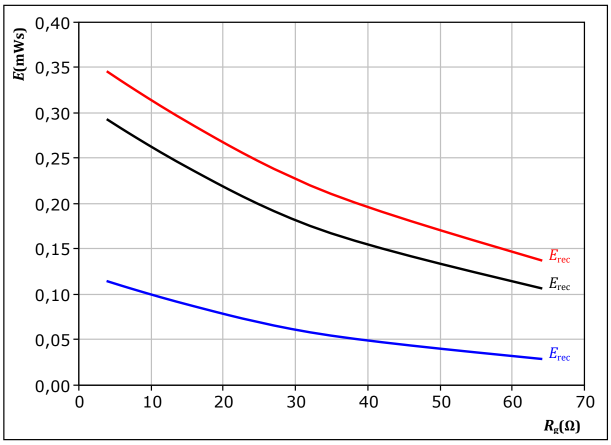
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 16 Ω

T_j:
25 °C
125 °C
150 °C

figure 23. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

E_{rec} = f(R_g)



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

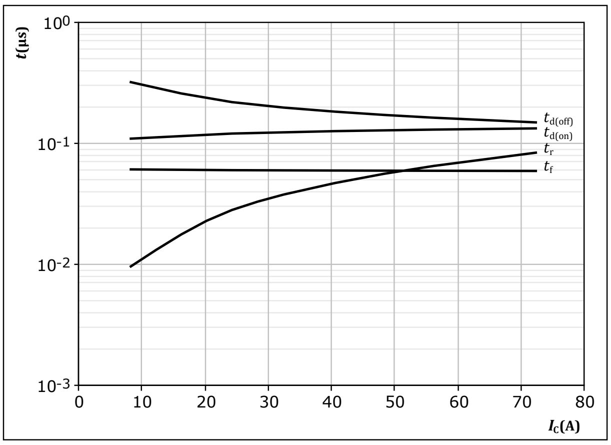
T_j:
25 °C
125 °C
150 °C

Inverter Switching Characteristics

figure 24. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



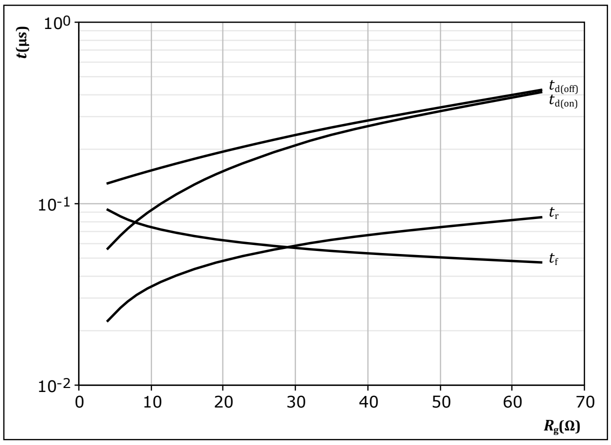
With an inductive load at

T_j = 150 °C
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 16 Ω
R_{goff} = 16 Ω

figure 25. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



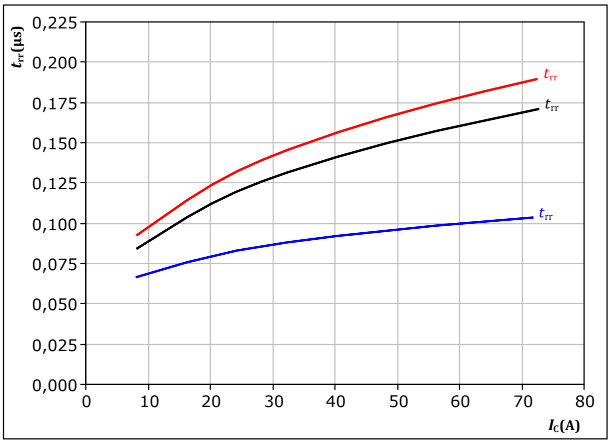
With an inductive load at

T_j = 150 °C
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

figure 26. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

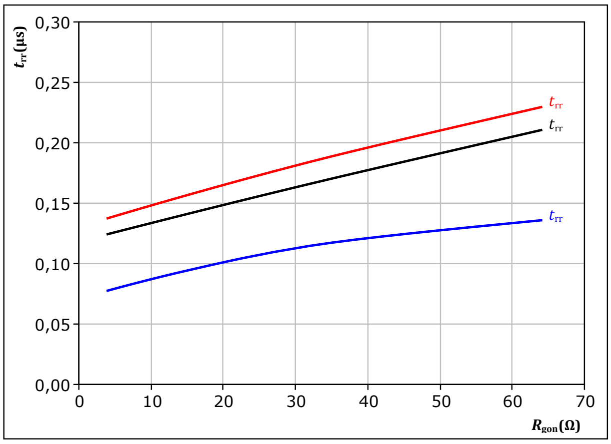
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 16 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 27. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

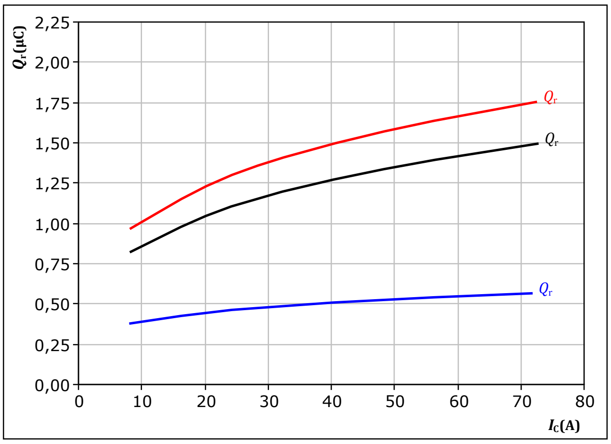
T_j:
— 25 °C
— 125 °C
— 150 °C

Inverter Switching Characteristics

figure 28. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



With an inductive load at

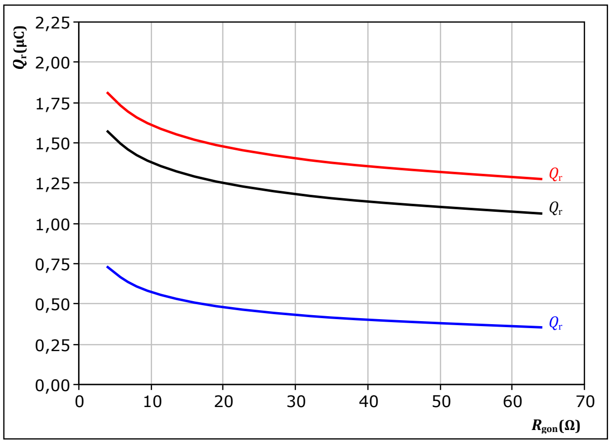
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 16 Ω

T_j:
25 °C
125 °C
150 °C

figure 29. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



With an inductive load at

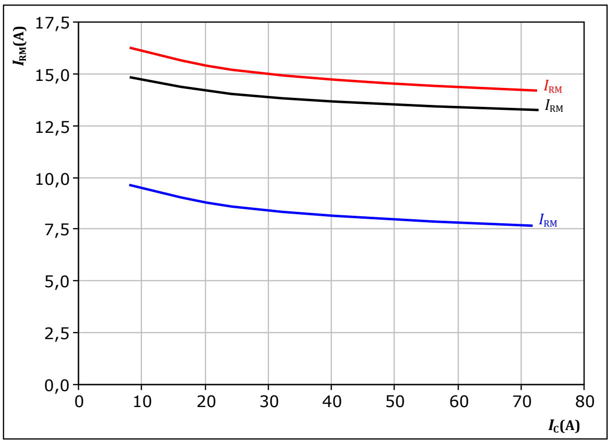
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

T_j:
25 °C
125 °C
150 °C

figure 30. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



With an inductive load at

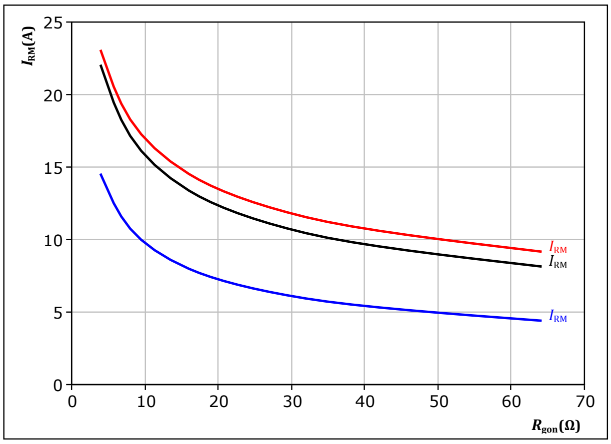
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 16 Ω

T_j:
25 °C
125 °C
150 °C

figure 31. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

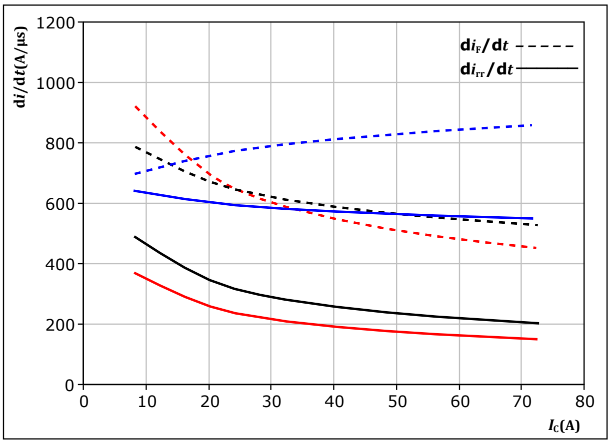
T_j:
25 °C
125 °C
150 °C

Inverter Switching Characteristics

figure 32. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



With an inductive load at

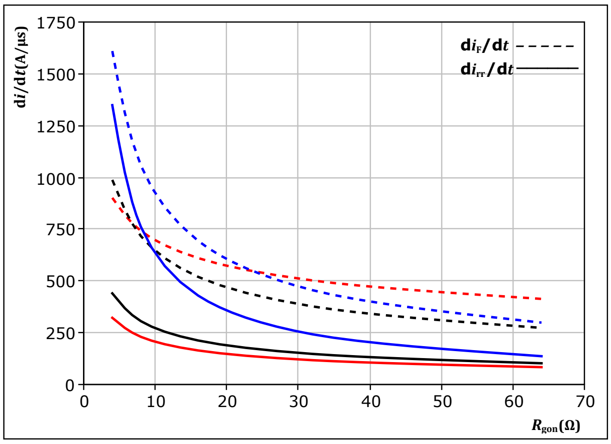
V_{CE} = 350 V
V_{GE} = ±15 V
R_{gon} = 16 Ω

T_j:
- 25 °C
- 125 °C
- 150 °C

figure 33. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



With an inductive load at

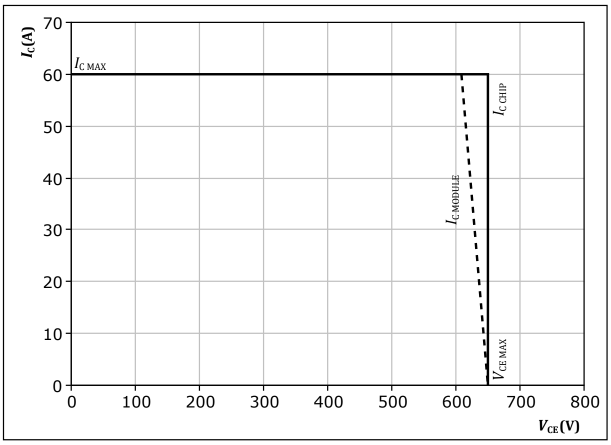
V_{CE} = 350 V
V_{GE} = ±15 V
I_C = 40 A

T_j:
- 25 °C
- 125 °C
- 150 °C

figure 34. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



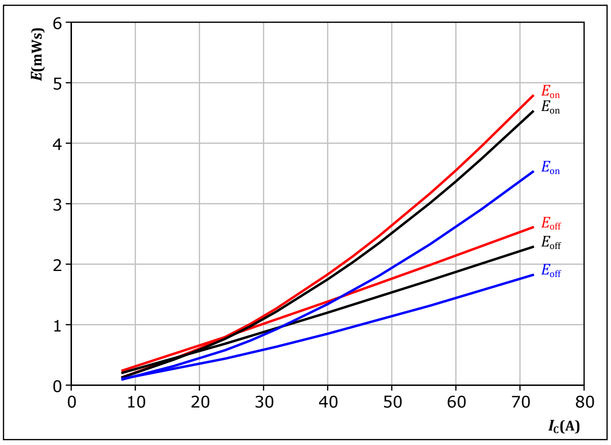
At
T_j = 150 °C
R_{gon} = 16 Ω
R_{goff} = 16 Ω

Brake Switching Characteristics

figure 35. **IGBT**

Typical switching energy losses as a function of collector current

E = f(I_C)



With an inductive load at

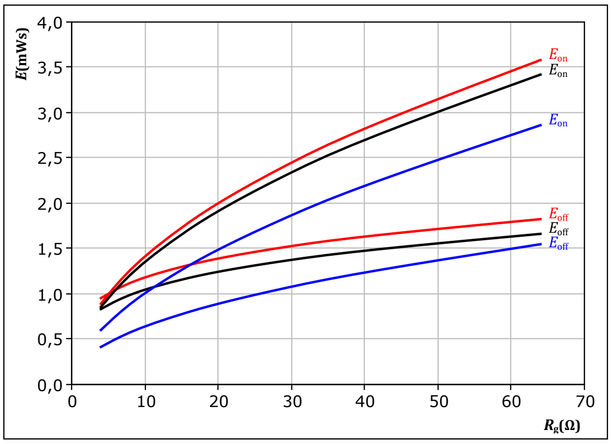
V_{CE} = 400 V
V_{GE} = 0/15 V
R_{gon} = 16 Ω
R_{goff} = 16 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 36. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

E = f(R_g)



With an inductive load at

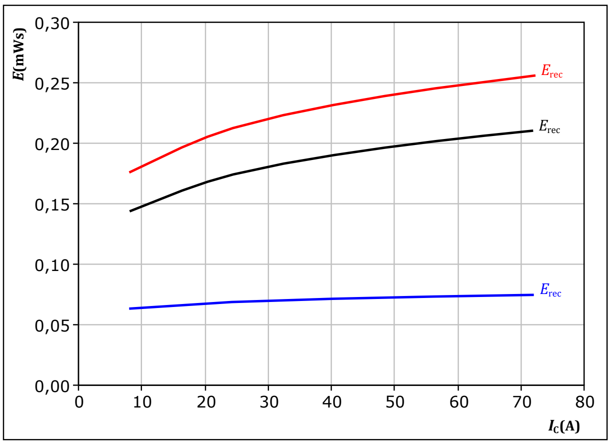
V_{CE} = 400 V
V_{GE} = 0/15 V
I_C = 40 A

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 37. **FWD**

Typical reverse recovered energy loss as a function of collector current

E_{rec} = f(I_C)



With an inductive load at

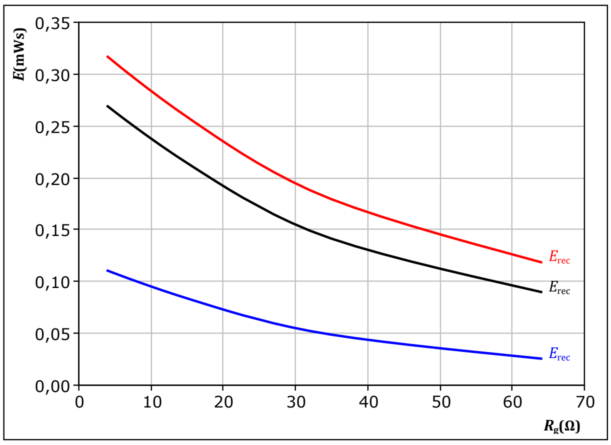
V_{CE} = 400 V
V_{GE} = 0/15 V
R_{gon} = 16 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 38. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

E_{rec} = f(R_g)



With an inductive load at

V_{CE} = 400 V
V_{GE} = 0/15 V
I_C = 40 A

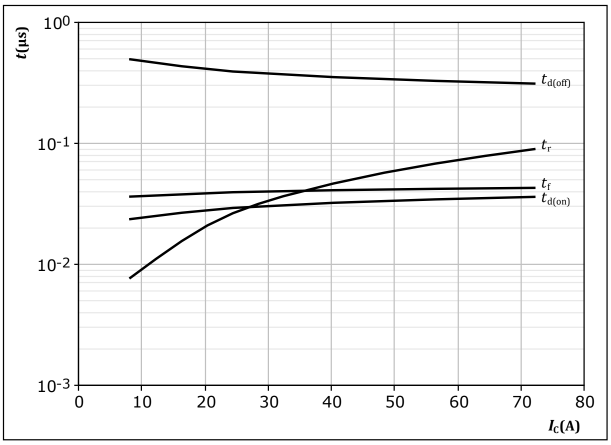
T_j:
— 25 °C
— 125 °C
— 150 °C

Brake Switching Characteristics

figure 39. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



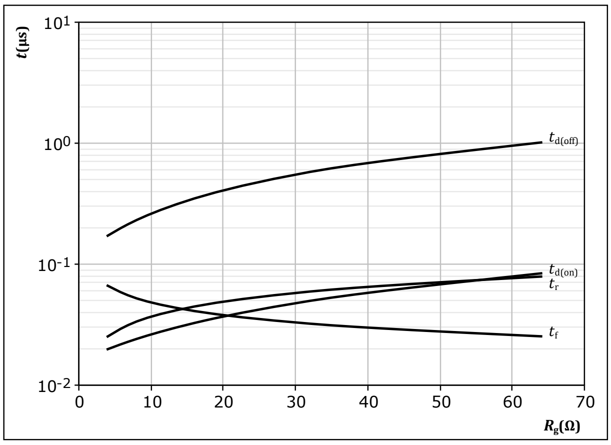
With an inductive load at

T_j = 150 °C
V_{CE} = 400 V
V_{GE} = 0/15 V
R_{gon} = 16 Ω
R_{goff} = 16 Ω

figure 40. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



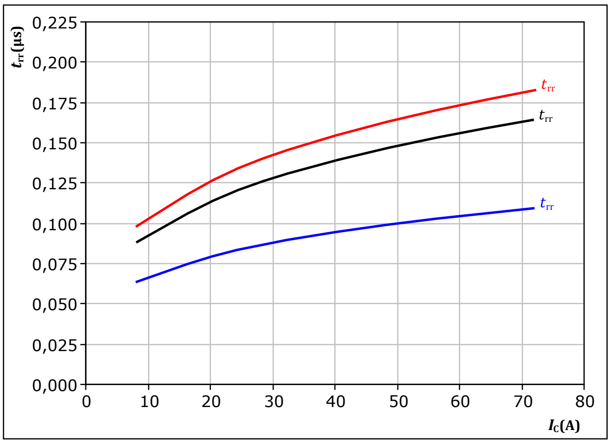
With an inductive load at

T_j = 150 °C
V_{CE} = 400 V
V_{GE} = 0/15 V
I_C = 40 A

figure 41. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

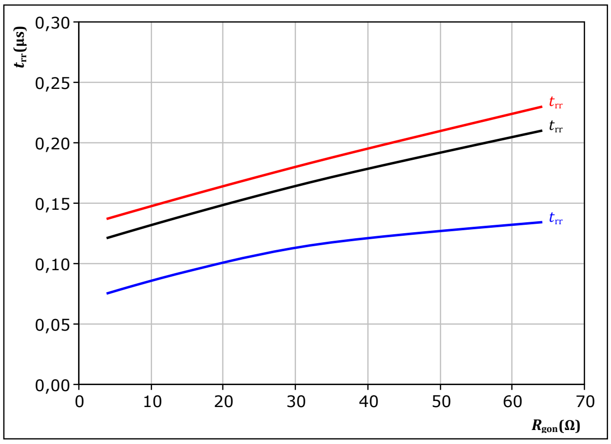
V_{CE} = 400 V
V_{GE} = 0/15 V
R_{gon} = 16 Ω

T_j:
— 25 °C
— 125 °C
— 150 °C

figure 42. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} = 400 V
V_{GE} = 0/15 V
I_C = 40 A

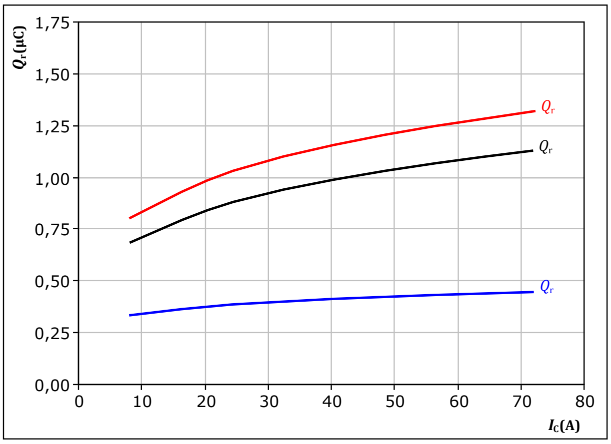
T_j:
— 25 °C
— 125 °C
— 150 °C

Brake Switching Characteristics

figure 43. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



With an inductive load at

V_{CE} = 400 V

V_{GE} = 0/15 V

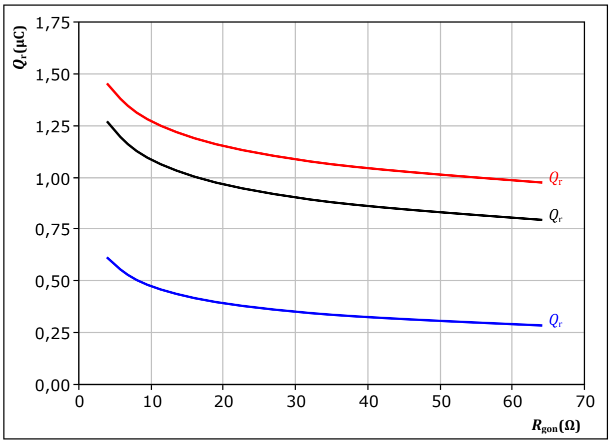
R_{gon} = 16 Ω

T_j: 25 °C / 125 °C / 150 °C

figure 44. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



With an inductive load at

V_{CE} = 400 V

V_{GE} = 0/15 V

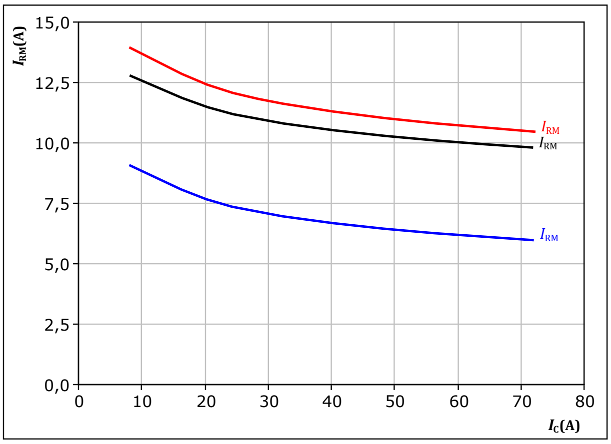
I_C = 40 A

T_j: 25 °C / 125 °C / 150 °C

figure 45. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



With an inductive load at

V_{CE} = 400 V

V_{GE} = 0/15 V

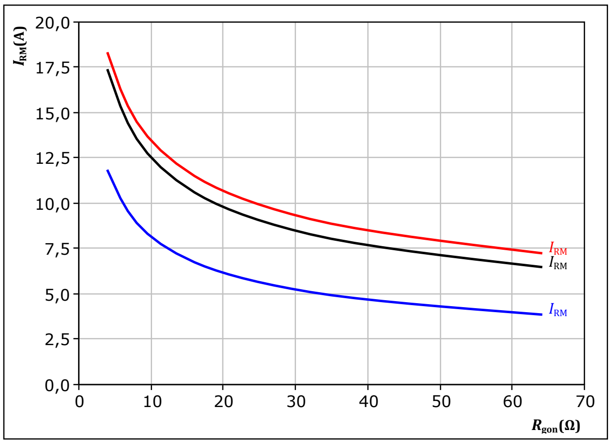
R_{gon} = 16 Ω

T_j: 25 °C / 125 °C / 150 °C

figure 46. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

V_{CE} = 400 V

V_{GE} = 0/15 V

I_C = 40 A

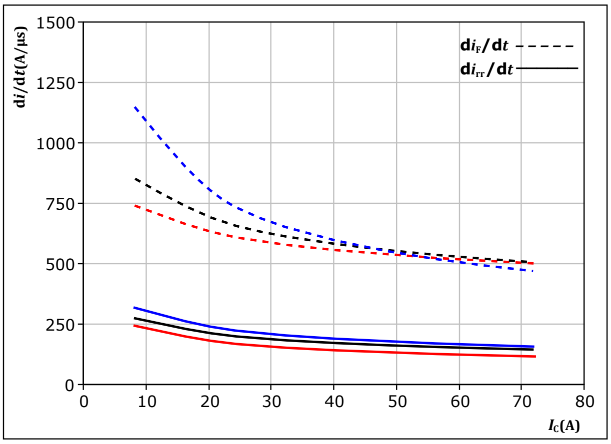
T_j: 25 °C / 125 °C / 150 °C

Brake Switching Characteristics

figure 47. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



With an inductive load at

V_{CE} = 400 V

V_{GE} = 0/15 V

R_{gon} = 16 Ω

T_j:

25 °C

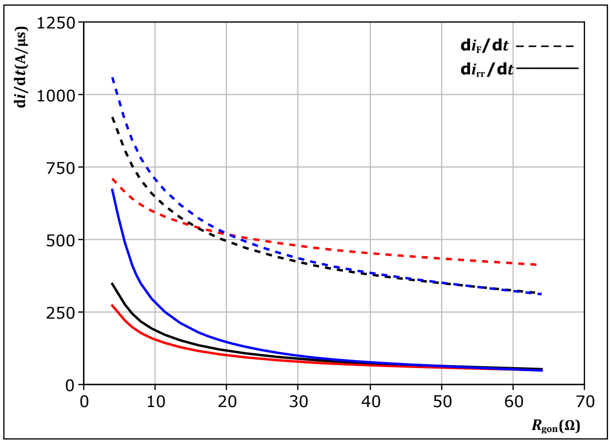
125 °C

150 °C

figure 48. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



With an inductive load at

V_{CE} = 400 V

V_{GE} = 0/15 V

I_C = 40 A

T_j:

25 °C

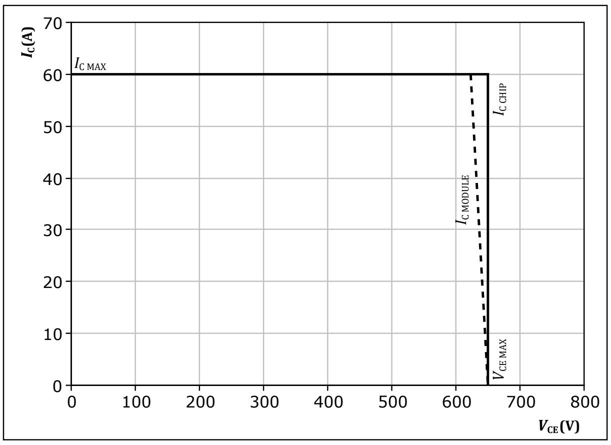
125 °C

150 °C

figure 49. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At T_j = 150 °C

R_{gon} = 16 Ω

R_{goff} = 16 Ω

Switching Definitions

figure 50. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = integrating time for E_{off})

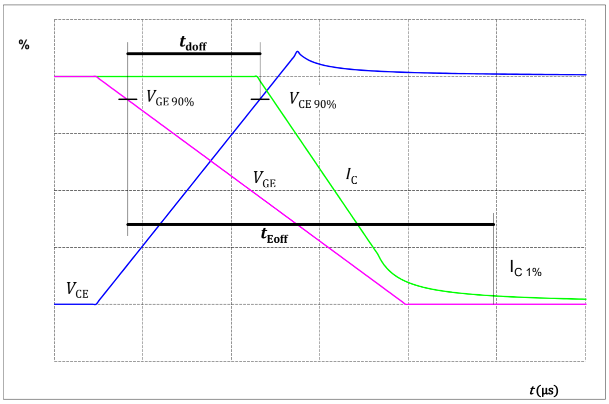


figure 51. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

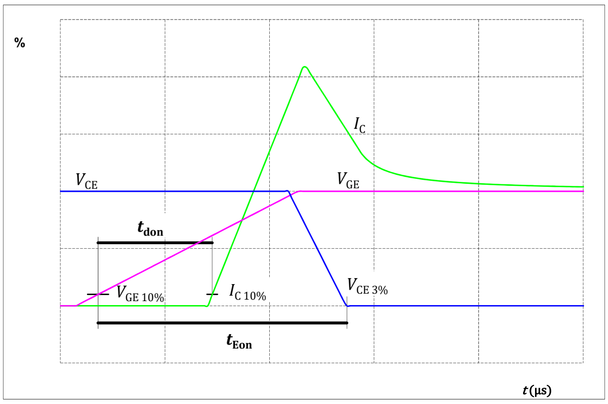


figure 52. **IGBT**

Turn-off Switching Waveforms & definition of t_{f}

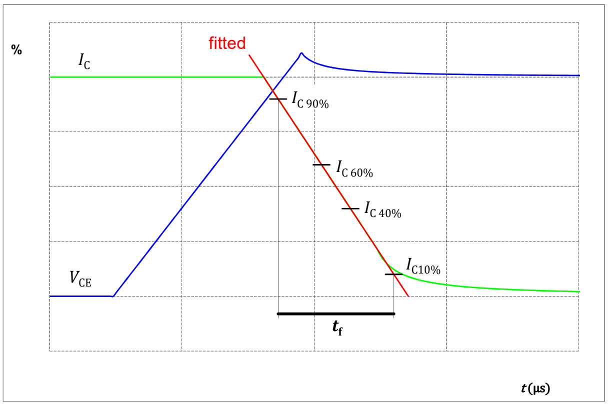
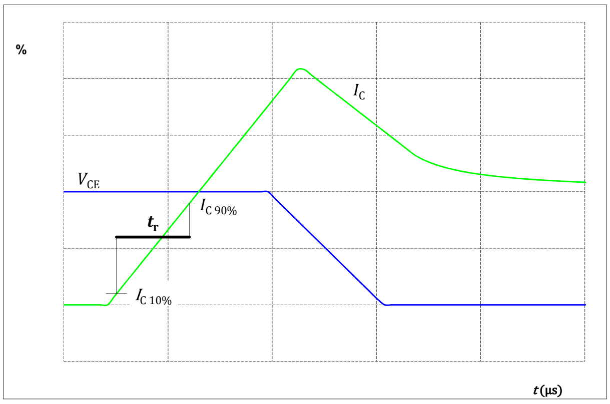


figure 53. **IGBT**

Turn-on Switching Waveforms & definition of t_{r}



Switching Definitions

figure 54. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

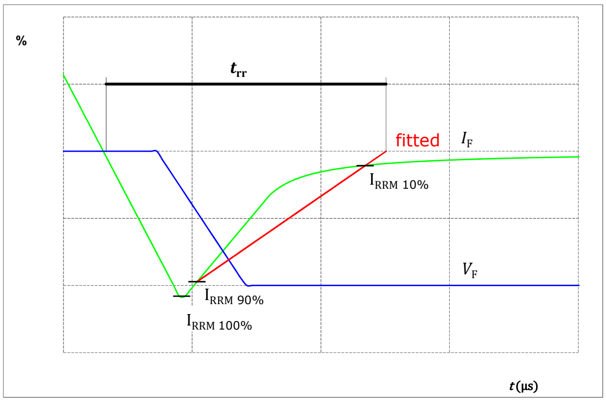
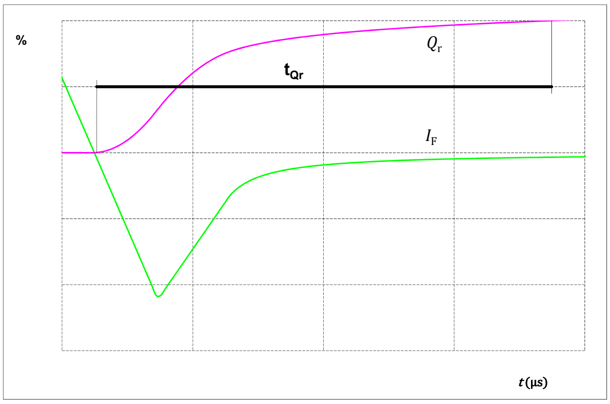


figure 55. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

Version	Ordering Code
Without thermal paste	10-EZ07PMA030I7-L926A28T
With thermal paste (5,2 W/mK, PTM6000HV)	10-EZ07PMA030I7-L926A28T-/7/

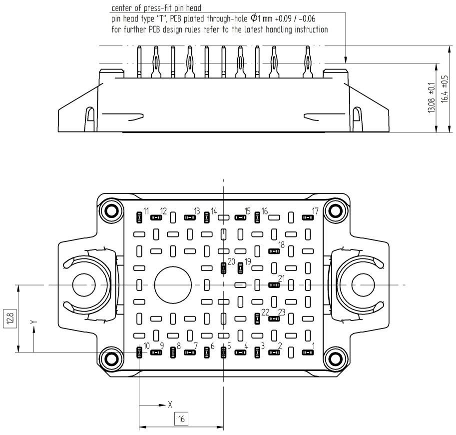
Marking

		Name		Date code	UL & VIN	Lot	Serial
	**Text**	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

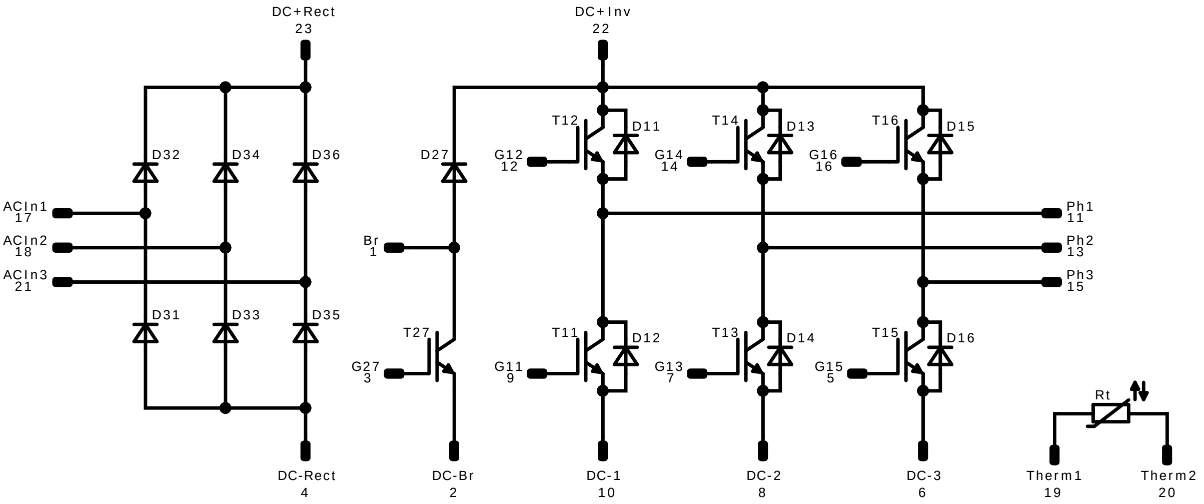
Pin table [mm]

Pin	X	Y	Function
1	32	0	Br
2	25,6	0	DC-Br
3	22,4	0	G27
4	19,2	0	DC-Rect
5	16	0	G15
6	12,8	0	DC-3
7	9,6	0	G13
8	6,4	0	DC-2
9	3,2	0	G11
10	0	0	DC-1
11	0	25,6	Ph1
12	3,2	25,6	G12
13	9,6	25,6	Ph2
14	12,8	25,6	G14
15	19,2	25,6	Ph3
16	22,4	25,6	G16
17	32	25,6	ACIn1
18	25,6	19,2	ACIn2
19	19,2	16	Therm1
20	16	16	Therm2
21	25,6	12,8	ACIn3
22	22,4	6,4	DC+Inv
23	25,6	6,4	DC+Rect



Tolerance of pinpositions: ±0.4mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	650 V	30 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	650 V	30 A	Inverter Diode	
T27	IGBT	650 V	30 A	Brake Switch	
D27	FWD	650 V	20 A	Brake Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	28 A	Rectifier Diode	
Rt	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E1 packages see vincotech.com website.

Package data
Package data for *flow* E1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-EZ07PMA030I7-L926A28T-D1-14	2 Oct. 2025	Initial Release	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.